EUCARD²; Sub-task 12.5.1 Pb photocathode deposition for improved performance of SRF guns

status in April 2014

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Contents:

- Obligations: sub-task12.5.1
- Methods of upgrading thin-layer phtotocathode morphology
 - Non-filtered deposition + remelting
 - Filtered deposition
- -Diagnostic stand
- Vacuum annealing

Obligation



Workpackage: WP12 Innovative RF technologies

Task: WP12.5 Photocathodes

Pb photocathode deposition for improved performance of

SRF guns

deposition improvement, post-deposition treatment, Q and QE measurements

Milestone

MS80 Demonstrated operation of improved deposition system, Pb layers of $\underline{1-2}$ μm in thickness

M30

Report on samples characterisation NCBJ

Deliverables

D12.8 Optimised procedure for microdorplets flattening with an UV laser

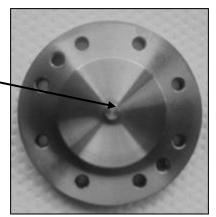
M36

Report NCBJ

D12.9 Pb/Nb plug photocathodes — measurements and characterization.

M42

Report HZDR (+DESY + NCBJ)

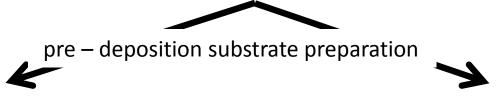




Approach to Eucard 2



To improve Pb photocathode preparation

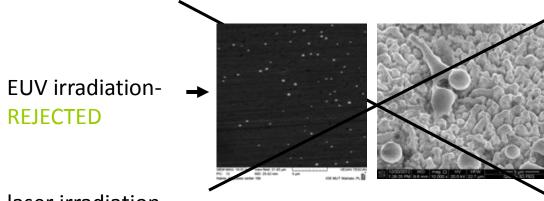


Deposition system reconstruction to find better compromise between thickness and low micro-droplets population

micro-droplets filter developement

MS 80

Post-deposition flattening:



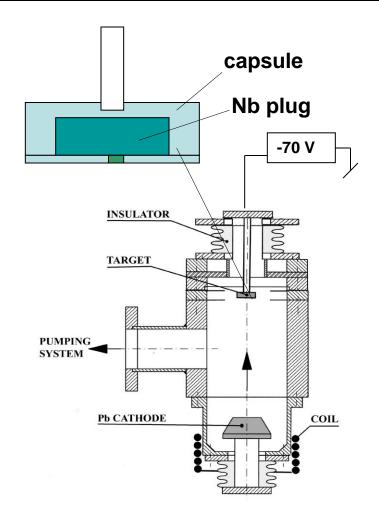
laser irradiation plasma ion pulses irradiation annealing

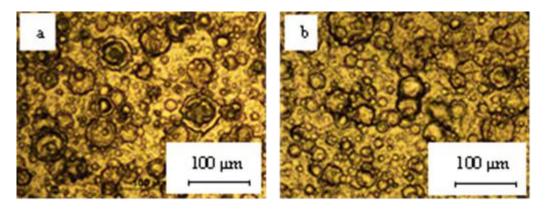
D12.8

First approach: lead deposition in a short non-filtered arc









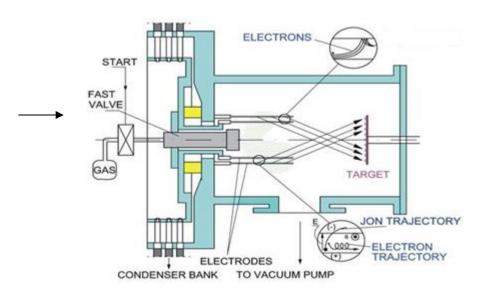
arc current 25 A, (pulse length 5-20 s.)
cathode-target distance 10 cm
substrate bias -70 v − energetic deposition
current to the target dens. ≈ 42 mA/cm²
Pb deposition rate ≈ 3 μm/min
substrate: Nb, Pb sapphire samples
no droplets filtering − droplets density

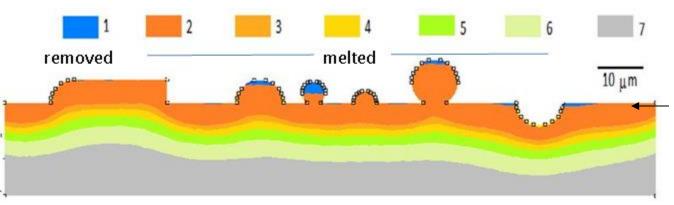
First approach: melting and recrystalization with ion pulses





Plasma source: Rod Plasma Injector IBIS
The RPI-IBIS device was equipped with two
coaxial electrodes composed of 32 thin metallic
rods placed inside a vacuum chamber, which was
pumped out to the background pressure equal to
about 10⁻⁶ Pa. Before each discharge the interelectrode gap was filled up with some amount of
Ar injected by a fast acting valve. with a chosen
delay advance to the discharge. During the
discharge the working gas, after its ionization,
was accelerated in the injector and emitted along
the z-axis towards Pb/Nb target in a form of an
intense plasma-ion stream.





Heat transfer evaluation by FEM for typical arc deposited film surface morphology:

- •single 3 J/cm² pulse removes lead from droplets but not from the flat surface
- •melts c.a 10µm in depth

First approach: melting and recrystalization with ion pulses in practice

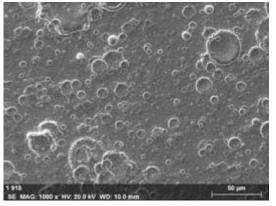


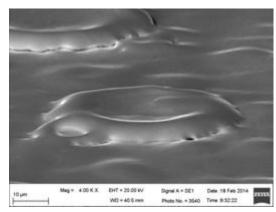
UHV arc deposited 2 μm thick Pb layer on EP niobium substrate (RRR>300):

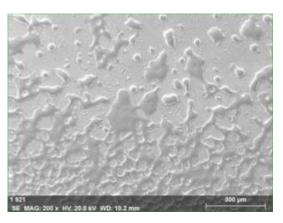
deposition

exposed to 6 Ar⁺pulses 1.5J/cm²

exp. to 3 pulses 2.5 J/cm²







Remelting and flattening of extrusions on the surface of a Pb layer with low-fluency 1.5 J/cm² ion pulses is effective only for extrusion smaller than \approx 20 µm. After applying ion pulses of 2.5 – 3 J/cm² fluency the layer is melted completely forming a non-uniformly spread "labirynth" with most of the Nb surface deprived of lead. It results from poor niobium wettability with molten Pb.

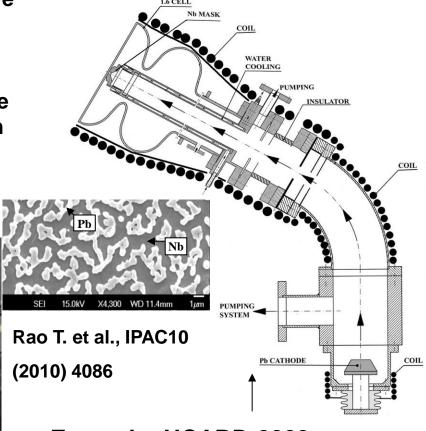
Considered remedies - improving Pb to Nb adhesion by preliminary treatment in the IBIS RPI:

- introducing Pb ions from rod electrodes into Nb substrate and remelting
- Pb ions implantation into a Nb substratr, creating an intermediate layer

Second approach: Pb deposition in UHV arc with droplets filtering



Angular magnetic filters designed to remove droplets from plasma stream before deposition. Metal plasma is guided by axial magnetic field along a curved plasma duct. Most of the droplets strike the duct wall due to high mass-to-charge ratio. Some of them are dissipated and reach the target.



Example: UCARD 2009:

filtered UHV arc system used for Pb photocathode deposition directly on the back wall of a 1.6 Nb cell It resulted in thin (100 nm) layer of poor adhesion (no energetic deposition possible, no neg. bias of target).

Second approach: Pb deposition in UHV arc with droplets filtering



Using UHV arc lead deposition with 30° angular filter, extended plasma duct and movable, negatively biased target. Optimization of target position to reach flat layer at sufficient deposition rate.

Dep. time 1000 s., ≈ 5 prticles/mm^{2,} Peeling products up to 120 μm

20 keV EDS results (SEM):

Pb: 92.9 wt %

Nb: 4.4 wt %

C: 1.8 wt %

O: 0.9 wt %

Dep. time 800 s.,

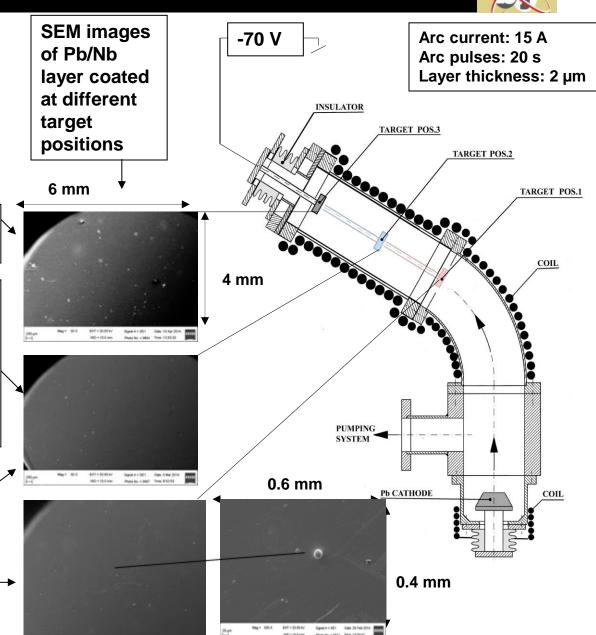
5 prticles/mm^{2,}

 $10 \mu m < drop size < 20 \mu m$

Dep. time 660 s.,

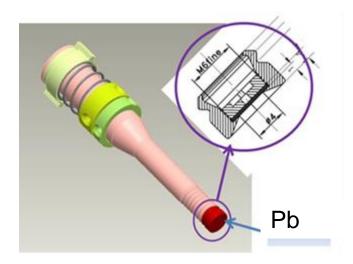
8 prticles/mm^{2,}

 $10 \, \mu m < drop size < 40 \, \mu m$



Pb/Nb thin layer photocathodes at HZDR





HZDR: four Nb plugs has been

- fabricated
- polished and cleaned
- sent to NCBJ Swierk for Pb deposition

NCBJ: the Nb plugs were Pb UHV arc deposited up to 2 µm using 30° angular droplets filter. One of the plugs was additionally treated with three 1.4 J/cm² Ar+ pulses in the IBIS rod plasma injector. The plugs were sent back to HZDR for tests in ELBE SRF gun (black current and QE). The results are not known yet.

Pb/Nb photocathodes diagnostic stand at NCBJ is being developed

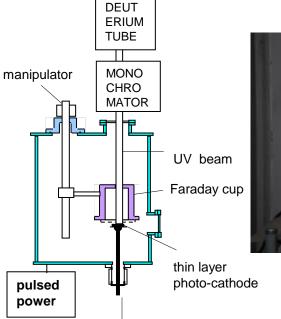


Photocathode diagnostic stand (schematic):

- -planned: photocathode, Faraday cup with transparent mesh anode, integrated deuterium tube + monochromator;
- -possessed: UHV chamber
- ordered: FC and photocathode manipulators
- -high voltage pulsed power supply (preliminarily tested);

Diagnostic stand schematic

12.5 kV pulsed power supply

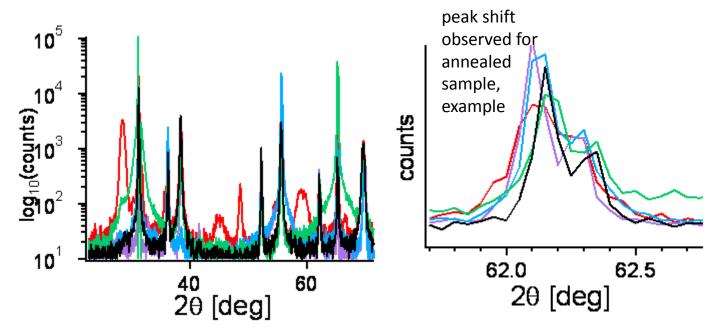




Post- deposition treatment – vacuum annealing







X-ray diffraction on Pb/Nb layers treated with various plasma pulses and with long time annealing (black curve):

- strain relaxation with annealing only,
- various surface orientations preffered

It comes from XRD measurements and heat calculs that pulse melting and recrystallization do not remove the strains induced during an arc deposition, this can be done by long time annealing.

Publications 3013



1. R. Nietubyć, J. Lorkiewicz, R. Mirowski, M. Barlak, J. Witkowski, J. Sekutowicz Recent development in optimization of superconducting thin film lead photocathodes at NCBJ Świerk

Proc. SPIE 8903 (2013) 89032B

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2. J. Lorkiewicz, R. Nietubyć, M. Barlak, R. Mirowski, A. Bartnik, J. Kostecki, J. Sekutowicz, A. Malinowska, P. Kneisel, J. Witkowski *Deposition and optimization of thin lead layers for superconducting accelerator photocathodes* Physica Scripta T (in press)

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